



## Correction to: Noise Characterization of InAs Based Composite Channel DG -MOSHEMT with Different Gate Dielectrics

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### Correction to: Silicon

<https://doi.org/10.1007/s12633-021-00954-3>

The original version of the article unfortunately contained an error.

The affiliation of the corresponding author is quoted wrong. The correction should be:

G. Sujatha - Anna University, Chennai, Tamil Nadu, India

The affiliation of the third author should be:

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